

Title (en)

METHOD FOR PRODUCING A TRANSISTOR STRUCTURE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER TRANSISTORSTRUKTUR

Title (fr)

PROCEDE DE FABRICATION D'UNE STRUCTURE A TRANSISTORS

Publication

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Application

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Abstract (en)

[origin: WO2004040643A1] The invention relates to a method for producing a transistor structure, comprised of at least one first and one second bipolar transistor with different collector widths. The invention is characterized in that all junctions between differently doped regions have a sharp interface. A first collector region (2.1) is suited for use in a high-frequency transistor having high limit frequencies f_T , and a second collector region (2.2) is suited for use in a high-voltage transistor having increased breakdown voltages.

IPC 1-7

H01L 21/8222; **H01L 27/082**; **H01L 29/08**

IPC 8 full level

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